PROCESS CPD24

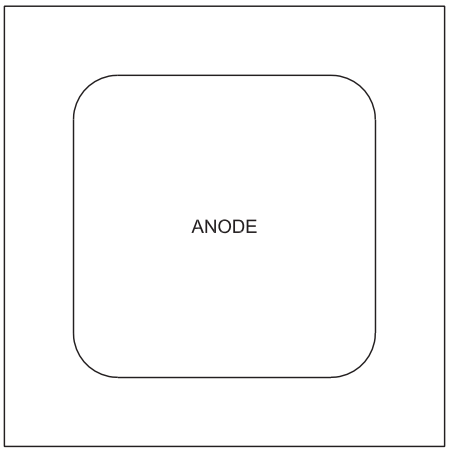
Fast Recovery Rectifier

1 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	11 MILS
Anode Bonding Pad Area	35 x 35 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE R1

GROSS DIE PER 4 INCH WAFER

4,250

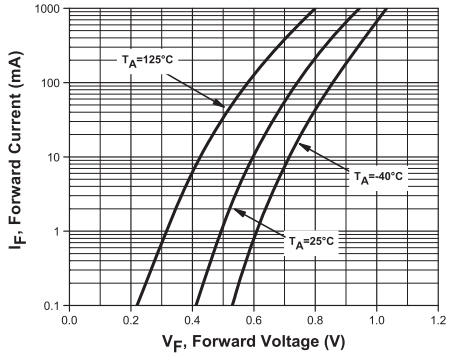
PRINCIPAL DEVICE TYPES

1N4933 thru 1N4937
1N4942 thru 1N4948
1N5615 thru 1N5623
CMR1F-02M Series

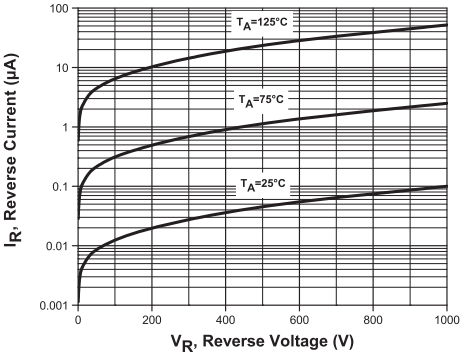
PROCESS CPD24

Typical Electrical Characteristics

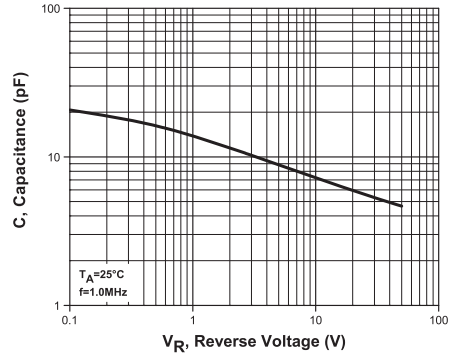
Forward Voltage



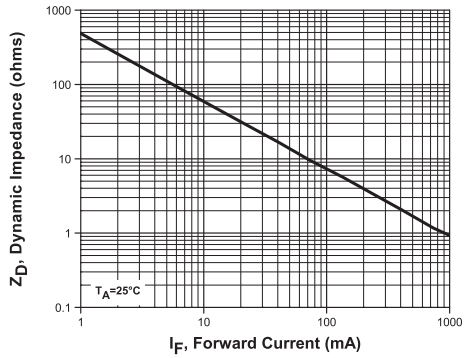
Leakage Current



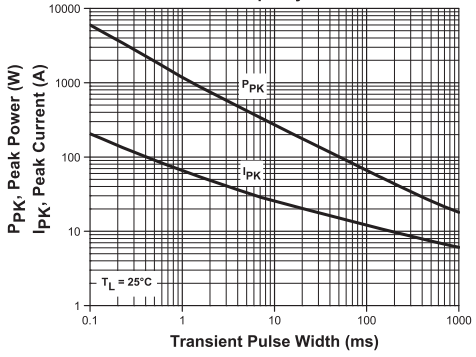
Capacitance



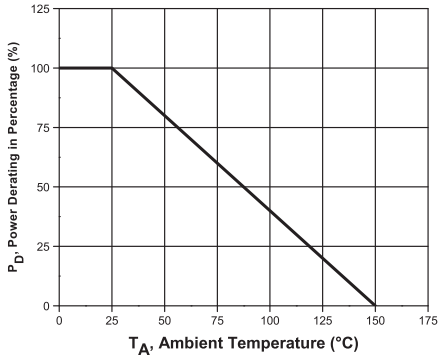
Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating



R3 (29-April 2010)